

Other important 1D operators (motivation: semiconductor devices)

charge density operator: i.e. an electron in state $|\psi\rangle$

charge density = $e|\psi(x)|^2$. Let's check units

$$\int |\psi(x)|^2 dx = 1, \text{ or } [|\psi(x)|^2] = L^{-1} \quad \square$$

charge density operator $\hat{\rho}(x)$: $\langle \rho(x) \rangle = e|\psi(x)|^2 = \langle \psi | \hat{\rho} | \psi \rangle$

$$\int f(x) \delta(x-a) dx = f(a) \quad \text{Dirac } \delta$$

$$\hat{\rho}(x) = e \delta(x-x') \quad \langle \psi | \hat{\rho} | \psi \rangle = e \int |\psi(x')|^2 \delta(x-x') dx' = e |\psi(x)|^2$$

current (density) operator

$$\hat{j}(x) = \frac{1}{2m} (\hat{p}_x \hat{\rho}(x) + \hat{\rho}(x) \hat{p}_x) \quad \text{with } \hat{p}_x = \frac{\hbar}{i} \frac{\partial}{\partial x}$$

e.g. in 1D: $\hat{j}(x) = -\frac{i\hbar}{2m} \left(\frac{d}{dx} \delta(x-x') + \delta(x-x') \frac{d}{dx} \right)$

$$\langle j(x) \rangle = \langle \psi | \hat{j} | \psi \rangle = -\frac{i\hbar}{2m} \left(\int_{-\infty}^{\infty} \psi^*(x') \frac{d}{dx} \delta(x-x') \psi(x') dx' + \int_{-\infty}^{\infty} \psi^*(x') \delta(x-x') \frac{d}{dx} \psi(x') dx' \right)$$

1st \int : by parts $\int u \frac{dv}{dx} dx = u v - \int v \frac{du}{dx} dx$

$$\int_{-\infty}^{\infty} \psi^*(x') \delta(x-x') \frac{d}{dx} \psi(x') dx' = -\psi(x) \frac{d}{dx} \psi^*(x)$$

2nd \int : $\psi^*(x) \frac{d}{dx} \psi(x)$

$$\langle j_x(x) \rangle = \frac{i\hbar}{2m} \left(\psi(x) \frac{d}{dx} \psi^*(x) - \psi^*(x) \frac{d}{dx} \psi(x) \right)$$

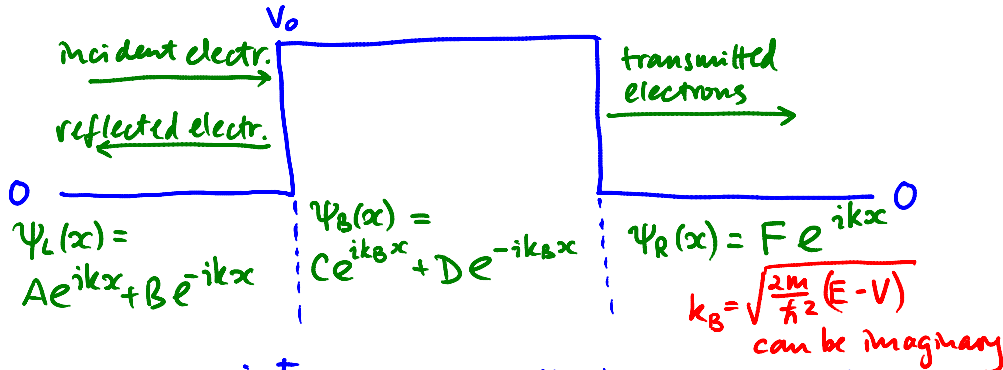
$[j_x] = \frac{Q}{T}$ - units of current in 1D (check)

Can show that expectation values satisfy charge conservation:

$$\frac{\partial}{\partial t} \langle \rho \rangle = -\frac{\partial}{\partial x} \langle j_x \rangle \quad \text{HW prob: prove for } \psi = \psi(x,t)$$

Note: $\psi(x,t)$ satisfies STDE

E.g. electrons tunneling thru a rectangular barrier



To the right:
$$j_x = \frac{i e \hbar}{2m} (F e^{ikx} (-ik) F^* e^{-ikx} - F^* e^{-ikx} ik F e^{ikx})$$

$$j_x = e |F|^2 \frac{\hbar k}{m}, \quad \frac{\hbar k}{m} \propto \frac{p}{m} = v \quad \text{- behaves like classical velocity}$$

To the left:
$$j_x = e \frac{\hbar}{2m} i \left(\psi_L \frac{d}{dx} \psi_L^* - \psi_L^* \frac{d}{dx} \psi_L \right) = e \frac{\hbar k}{m} (|A|^2 - |B|^2)$$

- $e |A|^2 v$ - incident current
- $e |B|^2 v$ - reflected current
- $e |F|^2 v$ - transmitted current
- $|A|^2 - |B|^2 = |F|^2$ - charge conservation

transmitted fraction more next lecture

$$\eta = \frac{|F|^2}{|A|^2} = \frac{|A|^2 - |B|^2}{|A|^2}$$

Effective mass (detour)

semiclassical eqn. of motion

$\langle v \rangle = \frac{\langle p \rangle}{m_0}$, get rid of mass: $E = \frac{\hbar^2 k^2}{2m_0}$ (free part.)

$$\langle v \rangle = \frac{1}{\hbar} \frac{dE(k)}{dk}$$

$$F_{ext} = \hbar \frac{dk}{dt}$$

$$\frac{dE}{dk} = \frac{\hbar(\hbar k)}{m_0}$$

$$a = \frac{dv}{dt} = \frac{1}{\hbar} \frac{d}{dt} \frac{dE(k)}{dk} = \frac{1}{\hbar} \frac{d^2 E(k)}{dk^2} \frac{dk}{dt} = \left[\frac{1}{\hbar^2} \frac{d^2 E(k)}{dk^2} \right] F_{ext}$$

$$m^* = m_{eff} = \hbar^2 \left(\frac{d^2 E(k)}{dk^2} \right)^{-1}$$

m^* is usually given in units of m_0

- periodic potential in crystals affect $E(k) \neq \frac{\hbar^2 k^2}{2m_0}$
- effective mass allows to retain much classical intuition (more when we get to solid state)

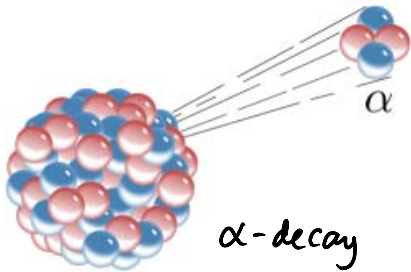
For 1D Hamiltonian $m_0 \rightarrow m^*_{eff}$ (if $m^* \neq m^*(x)$) we postulate

$$\hat{H} = -\frac{\hbar^2}{2} \frac{d}{dx} \left(\frac{1}{m_{eff}(x)} \frac{d}{dx} \right) + V(x)$$

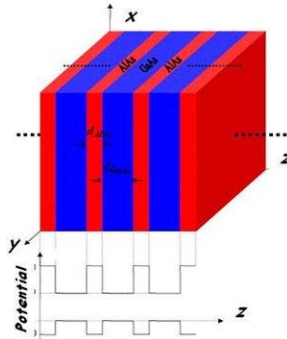
Tunneling :

many applications:

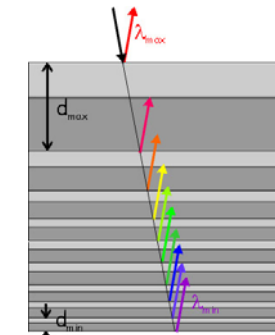
- charge transport in semiconductors
- field emission / photoemission } Richardson eqn.
- α -decay



α -decay

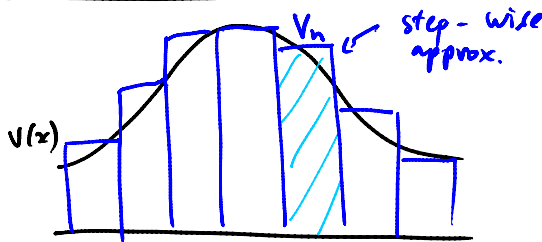


Superlattice (semiconductor devices)



multilayer optics (broadband mirrors)

Transfer matrix approach



x_n layer n x_{n+1} layer $n+1$
 $\rightarrow A_n$ $\rightarrow A_{n+1}$
 $\leftarrow B_n$ $\leftarrow B_{n+1}$
 width d_n $\Delta x = x - x_n$

$\psi_n(x) = A_n e^{ik_n \Delta x} + B_n e^{-ik_n \Delta x}$
 $k_n = \sqrt{\frac{2m_{eff}}{\hbar} (E - V_n)}$ ← can be imaginary

if can relate $\begin{pmatrix} A_n \\ B_n \end{pmatrix}$ to $\begin{pmatrix} A_{n+1} \\ B_{n+1} \end{pmatrix}$ ⇒ problem solved

$\psi_n(d_n) = A_n e^{ik_n d_n} + B_n e^{-ik_n d_n} = \psi_{n+1}(0) = A_{n+1} + B_{n+1}$ } wavefunction continuity
 $\frac{d}{dx} \psi_n(d_n) = \frac{d}{dx} \psi_{n+1}(0)$

$\frac{ik_n A_n e^{ik_n d_n} - ik_n B_n e^{-ik_n d_n}}{ik_{n+1}} = \frac{ik_{n+1} A_{n+1} - ik_{n+1} B_{n+1}}{ik_{n+1}}$

$A_{n+1} = \frac{1}{2} \left[A_n e^{ik_n d_n} \left(1 + \frac{k_n}{k_{n+1}}\right) + B_n e^{-ik_n d_n} \left(1 - \frac{k_n}{k_{n+1}}\right) \right]$

$$B_{n+1} = \frac{1}{2} \left[A_n e^{ik_n d_n} \left(1 - \frac{k_n}{k_{n+1}}\right) + B_n e^{-ik_n d_n} \left(1 + \frac{k_n}{k_{n+1}}\right) \right]$$

$$\begin{pmatrix} A_{n+1} \\ B_{n+1} \end{pmatrix} = T_n \begin{pmatrix} A_n \\ B_n \end{pmatrix}; \quad T_n = \begin{pmatrix} \frac{1}{2} \alpha_n (1 + \beta_n) & \frac{1}{2} \alpha_n^{-1} (1 - \beta_n) \\ \frac{1}{2} \alpha_n (1 - \beta_n) & \frac{1}{2} \alpha_n^{-1} (1 + \beta_n) \end{pmatrix}$$

To compute full matrix $T = T_n \dots T_2 T_1$

$$\alpha_n \equiv e^{ik_n d_n}, \quad \beta_n = \frac{k_n}{k_{n+1}}$$

Overall, for the entire potential barrier:

N - tot. number of slabs

$$\begin{pmatrix} A_N \\ B_N \end{pmatrix} = \begin{pmatrix} F \\ 0 \end{pmatrix} = T \begin{pmatrix} A \\ B \end{pmatrix}, \Rightarrow F = T_{11} A + T_{12} B$$

$$0 = T_{21} A + T_{22} B$$

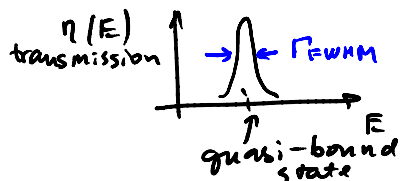
$$\text{transmission: } \left[\eta = 1 - \frac{|B|^2}{|A|^2} = \frac{|F|^2}{|A|^2} = 1 - \frac{|T_{21}|^2}{|T_{22}|^2} \right]$$

if effective mass changes $\beta_n \rightarrow \beta_n = \frac{k_n}{k_{n+1}} \frac{m_{\text{eff}, n+1}}{m_{\text{eff}, n}}$

Matlab example

Quasi-bound states

$\eta(E)$ displays peaks for finite walls @ quasi-bound



$$\Gamma_{\text{FWHM}} = \Delta E;$$

$$\tau \cdot \Gamma_{\text{FWHM}} \sim \hbar, \Rightarrow$$

$$\text{lifetime } \tau \sim \frac{\hbar}{\Gamma_{\text{FWHM}}}$$